

PHASE CHANGEABLE LAYERS INCLUDING PROTRUDING PORTIONS IN  
ELECTRODES THEREOF AND METHODS OF FORMING SAME

ABSTRACT

5        A structure in a phase changeable memory cell can include a bottom electrode having an interlayer dielectric layer thereon, the bottom electrode can have a recess therein that extends beyond a boundary between the bottom electrode and the interlayer dielectric. A phase changeable layer can be formed in the recess and include a protruding portion of the phase changeable layer that protrudes into the  
10      bottom electrode beyond the boundary. Related methods are also disclosed.